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2N7002BKS

60 V, 300 mA dual N-channel Trench MOSFET

Rev. 2 — 23 September 2010

Product data sheet

1. Product profile

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	±20	V
I_D	drain current	T_{amb} = 25 °C; V_{GS} = 10 V	[1] -	-	300	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 500 \text{mA}$	-	1	1.6	Ω

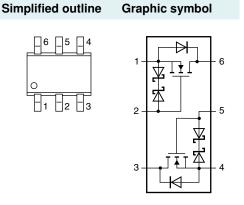
^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 300 mA dual N-channel Trench MOSFET

2. Pinning information

Table 2. **Pinning** Pin **Symbol** Description 1 S1 source 1 2 G1 gate 1 3 D2 drain 2 4 S2 source 2 G2 5 gate 2 6 D1 drain 1



017aaa055

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
2N7002BKS	SC-88	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
2N7002BKS	ZT*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	sistor				
V_{DS}	drain-source voltage	T _{amb} = 25 °C	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I_D	drain current	$V_{GS} = 10 \text{ V}$	<u>[1]</u>		
		T _{amb} = 25 °C	-	300	mA
		T _{amb} = 100 °C	-	215	mA

2N7002BK

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60 V, 300 mA dual N-channel Trench MOSFET

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$	-	1.2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] _	295	mW
			[1] -	340	mW
		T _{sp} = 25 °C	-	1040	mW
Source-di	rain diode				
I _S	source current	T _{amb} = 25 °C	<u>[1]</u> _	300	mA
ESD max	imum rating				
V_{ESD}	electrostatic discharge voltage	human body model	[3] _	2000	V
Per device	ce				
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] -	445	mW
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

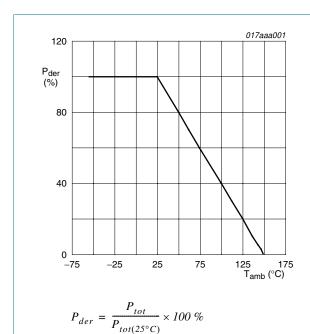
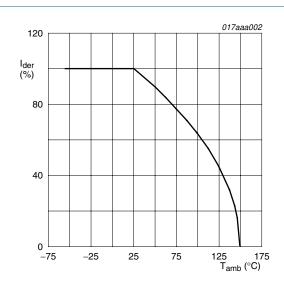


Fig 1. Normalized total power dissipation as a function of ambient temperature

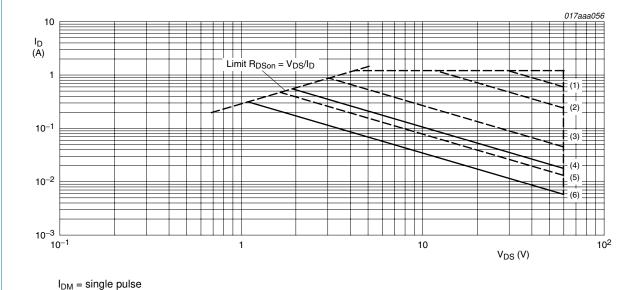


$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100~\%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

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60 V, 300 mA dual N-channel Trench MOSFET



- (1) $t_p = 100 \ \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; $T_{sp} = 25 \, ^{\circ}C$
- (5) $t_p = 100 \text{ ms}$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

Thermal characteristics 6.

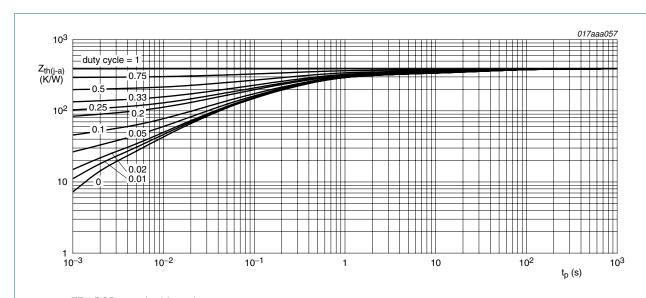
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
R _{th(j-a)} the	thermal resistance from	in free air	<u>[1]</u> -	370	425	K/W
	junction to ambient		[2] -	320	370	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	120	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	275	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

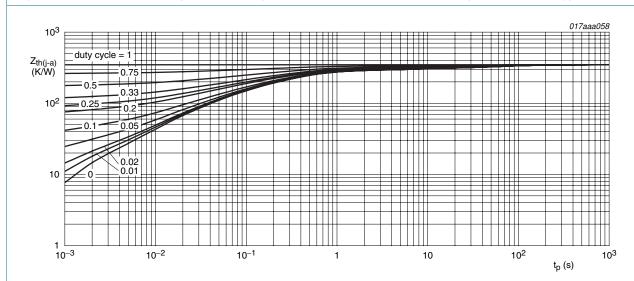
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

60 V, 300 mA dual N-channel Trench MOSFET



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 300 mA dual N-channel Trench MOSFET

7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \ \mu A; \ V_{GS} = 0 \ V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μА
		T _j = 150 °C	-	-	10	μА
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	10	μΑ
R _{DSon}	drain-source on-state resistance		<u>[1]</u>			
		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1.3	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 500 \text{ mA}$	-	1	1.6	Ω
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	[1] -	550	-	mS
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 300 \text{ mA};$	-	0.5	0.6	nC
Q_{GS}	gate-source charge	V _{DS} = 30 V; - V _{GS} = 4.5 V	-	0.2	-	nC
Q_{GD}	gate-drain charge	VGS = 4.5 V	-	0.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	33	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DD} = 50 \text{ V};$	-	5	10	ns
t _r	rise time	$R_L = 250 \Omega;$ - $V_{GS} = 10 V;$	-	6	-	ns
$t_{d(off)}$	turn-off delay time	$R_{G} = 6 \Omega$	-	12	24	ns
t _f	fall time		-	7	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	٧

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

60 V, 300 mA dual N-channel Trench MOSFET

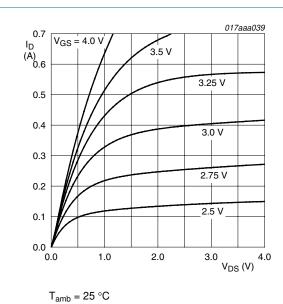
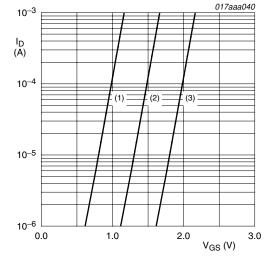


Fig 6. Output characteristics: drain current as a

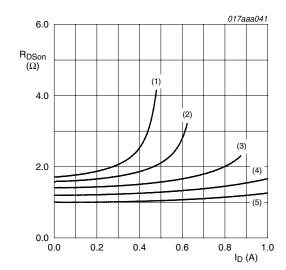
values



$$T_{amb}$$
 = 25 °C; V_{DS} = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

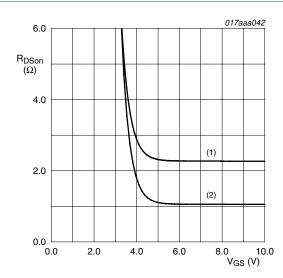


function of drain-source voltage; typical

T_{amb} = 25 °C

- (1) $V_{GS} = 3.25 \text{ V}$
- (2) $V_{GS} = 3.5 \text{ V}$
- (3) $V_{GS} = 4 V$
- (4) $V_{GS} = 5 V$
- (5) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values

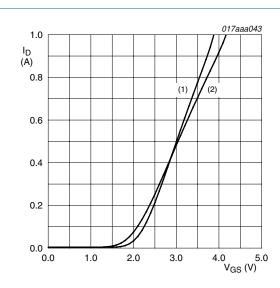


 $I_D = 500 \text{ mA}$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

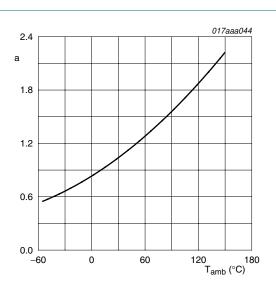
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$$V_{DS} > I_D \times R_{DSon}$$

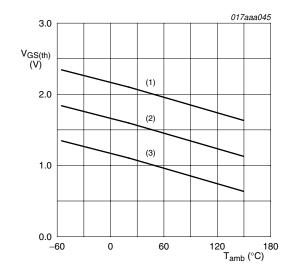
- (1) $T_{amb} = 25 \, ^{\circ}C$
- (2) $T_{amb} = 150 \, ^{\circ}C$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

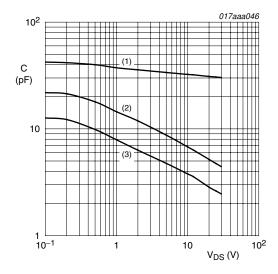
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of ambient temperature

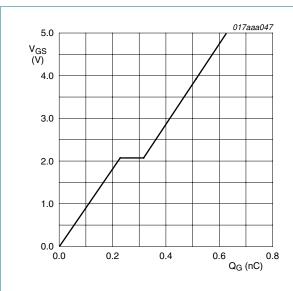


$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

60 V, 300 mA dual N-channel Trench MOSFET



 I_D = 300 mA; V_{DD} = 6 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

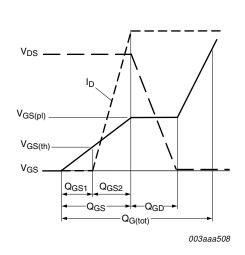
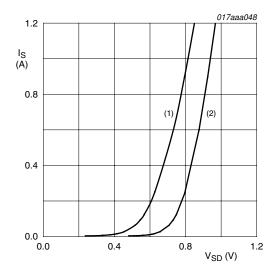


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

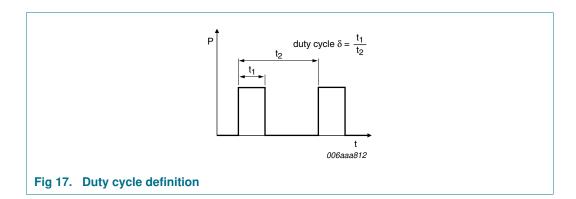
(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

60 V, 300 mA dual N-channel Trench MOSFET

8. Test information



60 V, 300 mA dual N-channel Trench MOSFET

9. Package outline

Plastic surface-mounted package; 6 leads

SOT363

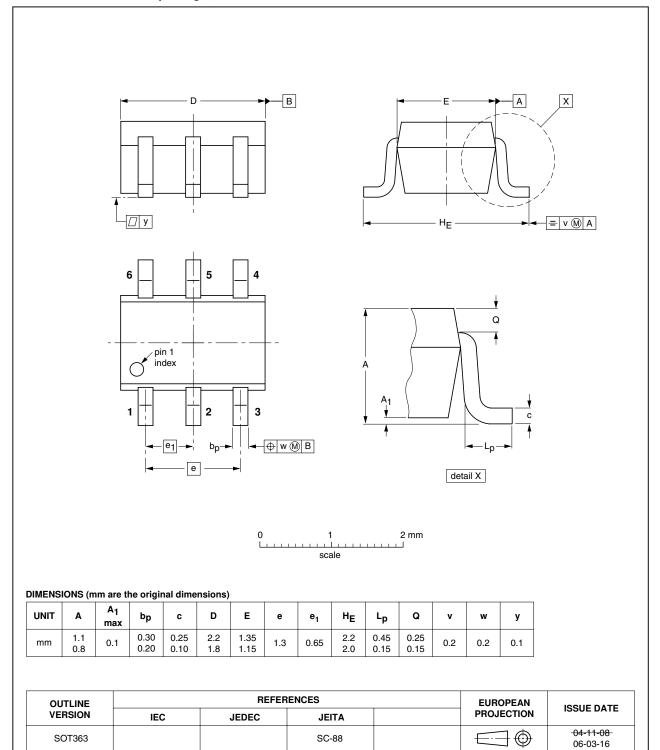


Fig 18. Package outline SOT363 (SC-88)

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10. Soldering

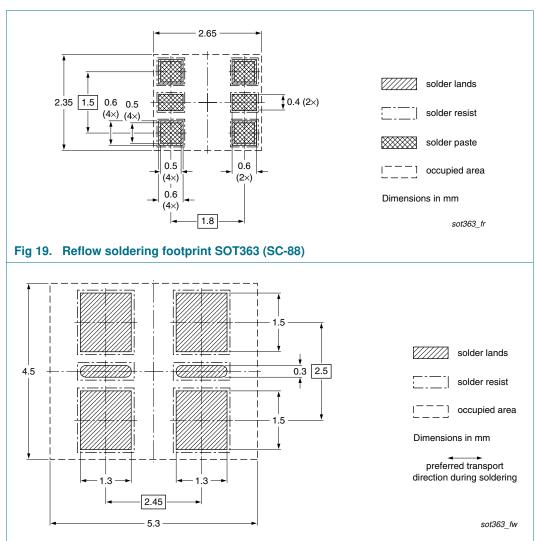


Fig 20. Wave soldering footprint SOT363 (SC-88)

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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002BKS v.2	20100923	Product data sheet	-	2N7002BKS v.1
Modifications:	• Table 2 "Pin	ning": graphic symbol amer	nded	
2N7002BKS v.1	20100617	Product data sheet	-	-

60 V, 300 mA dual N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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60 V, 300 mA dual N-channel Trench MOSFET

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2N7002BKS **NXP Semiconductors**

60 V, 300 mA dual N-channel Trench MOSFET

14. Contents

1	Product profile	. 1
1.1	General description	1
1.2	Features and benefits	
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	4
7	Characteristics	6
8	Test information	10
9	Package outline	11
10	Soldering	12
11	Revision history	13
12	Legal information	14
12.1	Data sheet status	14
12.2	Definitions	14
12.3	Disclaimers	14
12.4	Trademarks	15
13	Contact information	15
14	Contents	16

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